



60V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V(BR)DSS	R _{DS(on)}	I _D T _A = +25°C	
-60V	$390m\Omega @ V_{GS} = -10V$	-2.3A	
	595m Ω @ V _{GS} = -4.5V	-1.9A	

Description and Applications

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor Control
- **DC-DC Converters**
- Power Management Functions
- Uninterrupted Power Supply

Features and Benefits

- Fast Switching Speed
- Low Gate Drive
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

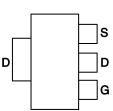
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (C3)
- Weight: 0.112 grams (Approximate)

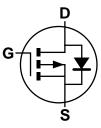


SOT223

Top View



Pin Out - Top View



Equivalent Circuit

Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMP6A13GTA	ZXMP6A13	7	12	1,000

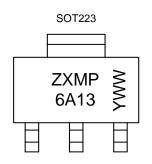
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied. 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"

Notes:

and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http:// www.diodes.com/products/packages.html.

Marking Information



ZXMP 6A13 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week Code (01~53)



Maximum Ratings (@T_A = +25°C unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	-60	V	
Gate-Source Voltage		V _{GS}	±20	V	
		(Note 6)		-2.3	
Continuous Drain Current $V_{GS} = 10V$	$V_{GS} = 10V$	$T_{A} = +70^{\circ}C$ (Note 6)	I _D	-1.9	А
		(Note 5)		-1.7	
Pulsed Drain Current	V _{GS} = 10V	(Note 7)	I _{DM}	-7.8	А
Continuous Source Current (Body Diode) (Note 6)		Is	-4.1	А	
Pulsed Source Current (Body Diode) (Note 7)		I _{SM}	-7.8	А	

Thermal Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 5)		2.0 16	W mW/°C	
Linear Derating Factor	(Note 6)	PD	3.9 31		
Thermal Registeres, Junction to Ambient	(Note 5)	P	62.5		
Thermal Resistance, Junction to Ambient	(Note 6)	R _θ JA	32.0	°C/W	
Thermal Resistance, Junction to Lead	(Note 8)	R _θ JL	9.8		
Operating and Storage Temperature Range		TJ, TSTG	-55 to 150	°C	

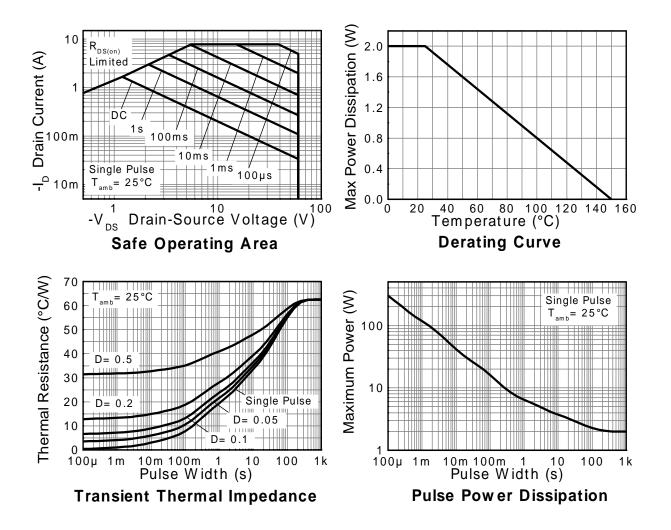
Notes: 5. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

6. Same as Note 5, except the device is measured at t \leq 10 sec.

Same as Note 5, except the device is pulsed with D = 0.02 and pulse width 300µs. The pulse current is limited by the maximum junction temperature.
Thermal resistance from junction to solder-point (at the end of the drain lead).



Thermal Characteristics





Electrical Characteristics (@T_A = +25°C unless otherwise specified.)

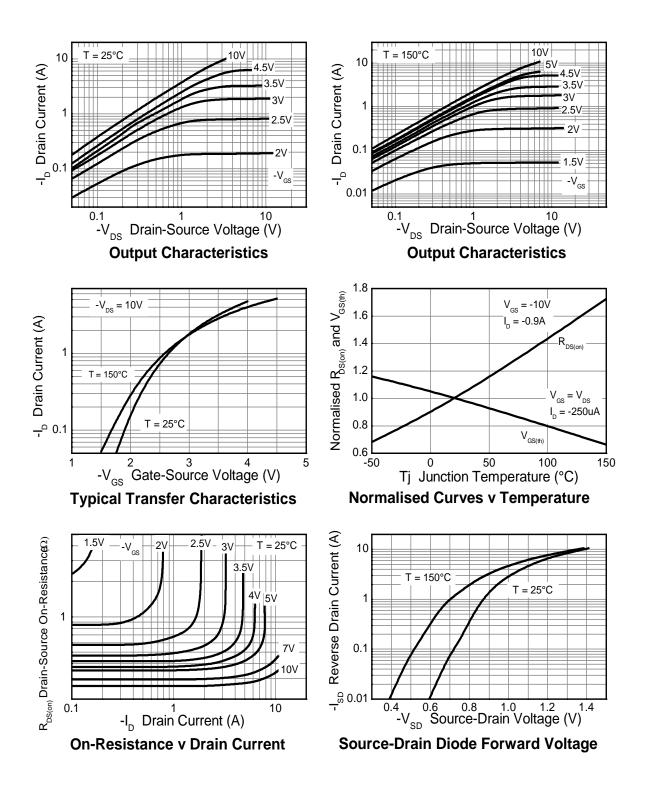
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	-60	_	—	V	$I_{D} = -250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-0.5	μA	$V_{DS} = -60V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_		±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(th)}	-1.0	-	-3.0	V	I _D = -250μA, V _I	os = V _{GS}
Static Drain-Source On-Resistance (Note 9)				0.390	Ω	V_{GS} = -10V, I_D	= -0.9A
Static Drain-Source On-Resistance (Note 9)	R _{DS} (ON)	_		0.595		V_{GS} = -4.5V, I_D	= -0.8A
Forward Transconductance (Notes 9 & 10)	g fs	_	1.8	_	S	V _{DS} = -15V, I _D = -0.9A	
Diode Forward Voltage (Note 9)	V _{SD}	_	-0.85	-0.95	V	$I_{S} = -0.8A, V_{GS} = 0V, T_{J} = +25^{\circ}C$	
Reverse Recovery Time (Note 10)	t _{rr}		21.1	_	ns	I _S = -0.9A, di/dt = 100A/µs, T _J = +25°C	
Reverse Recovery Charge (Note 10)	Qrr	_	19.3	—	nC		
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss	_	219	—	pF	V _{DS} = -30V, V _{GS} = 0V f = 1MHz	
Output Capacitance	Coss	_	25.7	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	20.5	_	pF		
Total Gate Charge (Note 11)	Qg	_	2.9	—	nC	$V_{GS} = -4.5V$	
Total Gate Charge (Note 11)	Qg	_	5.9	_	nC	$V_{\rm GS} = -10V$ $V_{\rm DS} = -30V$ $V_{\rm DS} = -0.9A$	
Gate-Source Charge (Note 11)	Q _{gs}	_	0.74	_	nC		
Gate-Drain Charge (Note 11)	Q _{gd}	_	1.5	_	nC		
Turn-On Delay Time (Note 11)	t _{D(on)}	_	1.6		ns	$V_{DD} = -30V, V_{GS} = -10V$ $I_D = -1A, R_G \cong 6.0\Omega$	
Turn-On Rise Time (Note 11)	tr	_	2.2		ns		
Turn-Off Delay Time (Note 11)	t _{D(off)}	_	11.2		ns		
Turn-Off Fall Time (Note 11)	tf	_	5.7	_	ns		

Notes:

9. Measured under pulsed conditions. Pulse width \leq 300µs; duty cycle \leq 2% 10. For design aid only, not subject to production testing. 11. Switching characteristics are independent of operating junction temperatures.

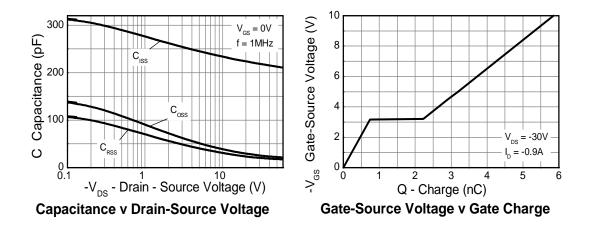


Typical Characteristics

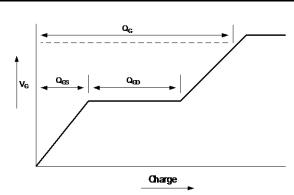




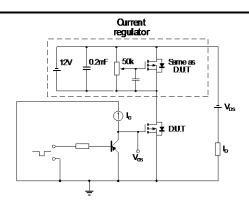
Typical Characteristics (cont.)



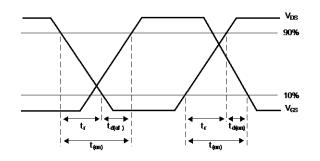
Test Circuits



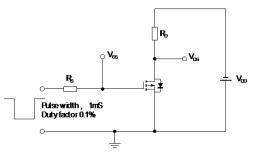
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms

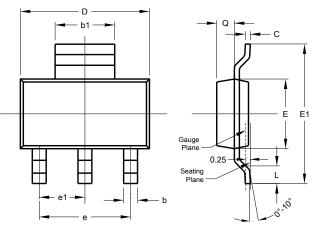


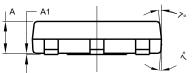
Switching time test circuit



Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

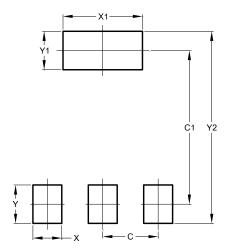




	SOT223					
Dim	Min	Max	Тур			
Α	1.55	1.65	1.60			
A1	0.010	0.15	0.05			
b	0.60	0.80	0.70			
b1	2.90	3.10	3.00			
С	0.20	0.30	0.25			
D	6.45	6.55	6.50			
E	3.45	3.55	3.50			
E1	6.90	7.10	7.00			
е	-	-	4.60			
e1	-	-	2.30			
L	0.85	1.05	0.95			
Q	0.84	0.94	0.89			
All I	All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



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